

SANYO	No. 4660A	2SA1883
		PNP Epitaxial Planar Silicon Transistor

**High-Speed
Switching Applications**

Features

- Fast switching speed.
- Low collector saturation voltage.
- High gain-bandwidth product.
- Small collector capacitance.
- Very small-sized package permitting 2SA1883-applied sets to be made small and slim.
- Complementary pair with the 2SC4987.

Absolute Maximum Ratings at Ta = 25°C

			unit
Collector to Base Voltage	V _{CB0}	-15	V
Collector to Emitter Voltage	V _{CEO}	-15	V
Emitter to Base Voltage	V _{EBO}	-5	A
Collector Current	I _C	-200	mA
Collector Current(Pulse)	I _{CP}	-500	mA
Base Current	I _B	-40	mA
Collector Dissipation	P _C	150	mW
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

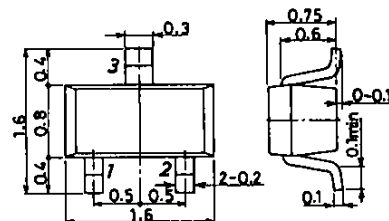
Electrical Characteristics at Ta = 25°C

			min	typ	max	unit
Collector Cutoff Current	I _{CB0}	V _{CB} = -8V, I _E = 0			-0.1	μA
Emitter Cutoff Current	I _{EBO}	V _{EB} = -3V, I _C = 0			-0.1	μA
DC Current Gain	h _{FE}	V _{CE} = -1V, I _C = -10mA	50	80	140	
Gain-Bandwidth Product	f _T	V _{CE} = -10V, I _C = -10mA	450	1000		MHz
Output Capacitance	C _{ob}	V _{CB} = -5V, f = 1MHz		1.8	3.0	pF
C-E Saturation Voltage	V _{CE(sat)}	I _C = -10mA, I _B = -1mA		-0.07	-0.20	V
B-E Saturation Voltage	V _{BE(sat)}	I _C = -10mA, I _B = -1mA		-0.80	-0.90	V
C-B Breakdown Voltage	V _{(BR)CBO}	I _C = -10μA, I _E = 0	-15			V
C-E Breakdown Voltage	V _{(BR)CEO}	I _C = -1mA, R _{BE} = ∞	-15			V
E-B Breakdown Voltage	V _{(BR)EBO}	I _E = -10μA, I _C = 0	-5			V
Turn-ON Time	t _{on}	See specified Test Circuit.		11		ns
Storage Time	t _{stg}	"		21		ns
Turn-OFF Time	t _{off}	"		19		ns

Marking : HA

Package Dimensions 2106A

(unit : mm)



1 : Base
2 : Emitter
3 : Collector

SANYO : SMCP

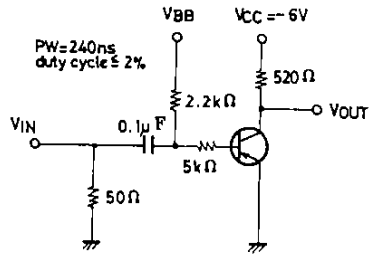
SANYO Electric Co., Ltd. Semiconductor Business Headquarters

TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110 JAPAN

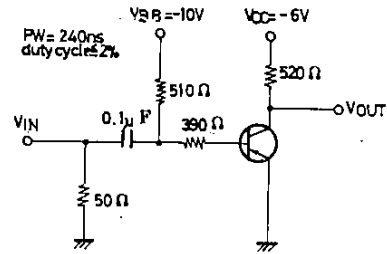
81094MT BX-1673, BX-0842 No.4660-1/4

Switching Time Test Circuit

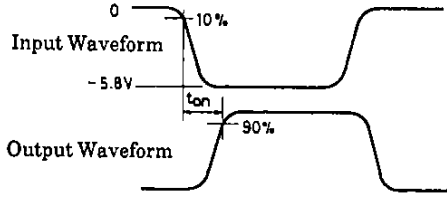
t_{on}, t_{off} Test Circuit



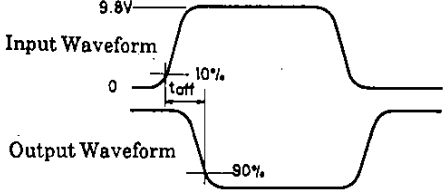
t_{stg} Test Circuit



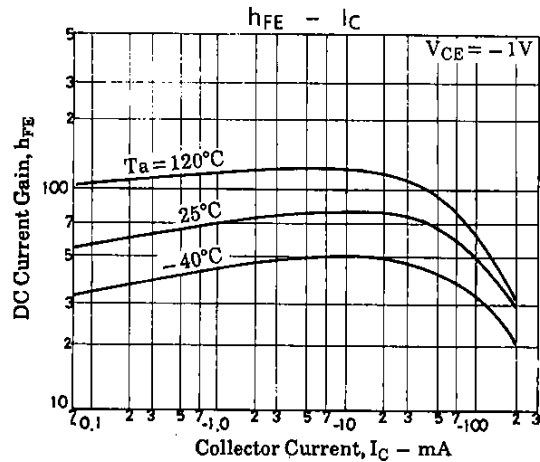
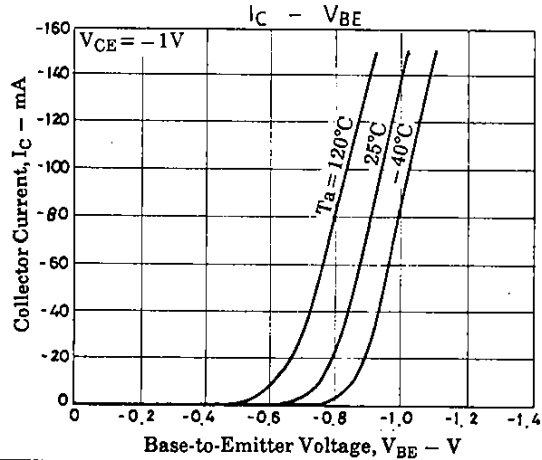
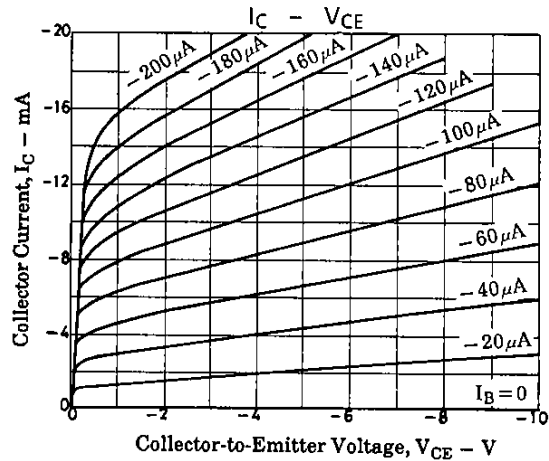
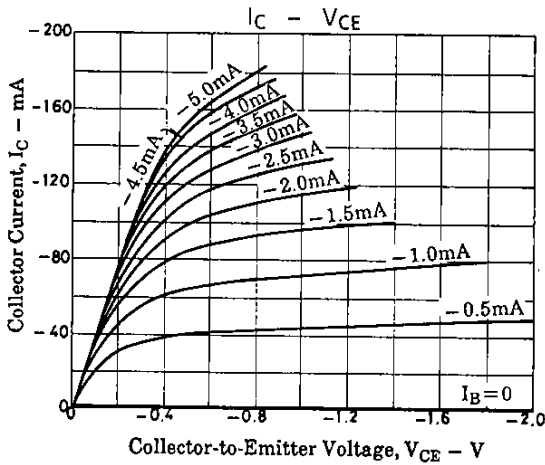
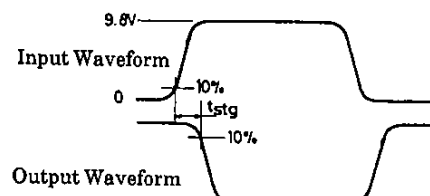
t_{on} Test Waveform ($V_{BB} = GND$)

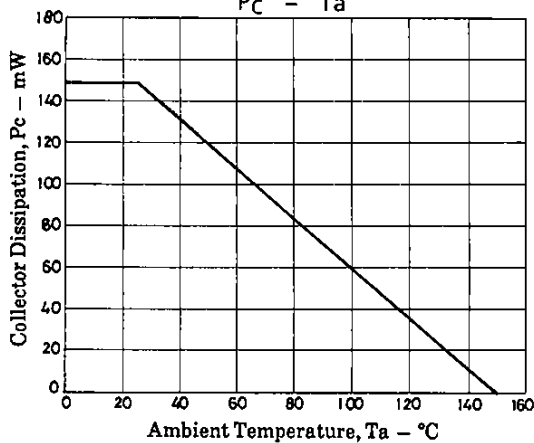
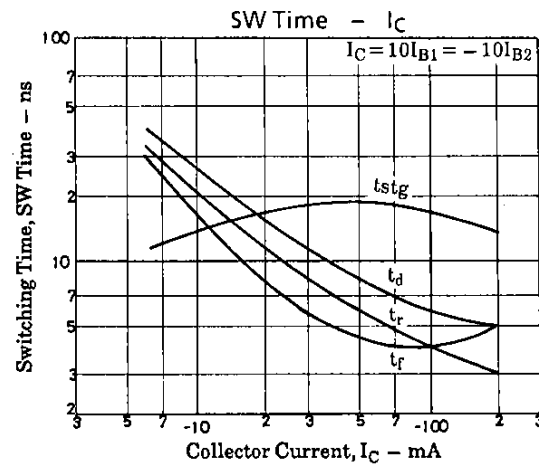
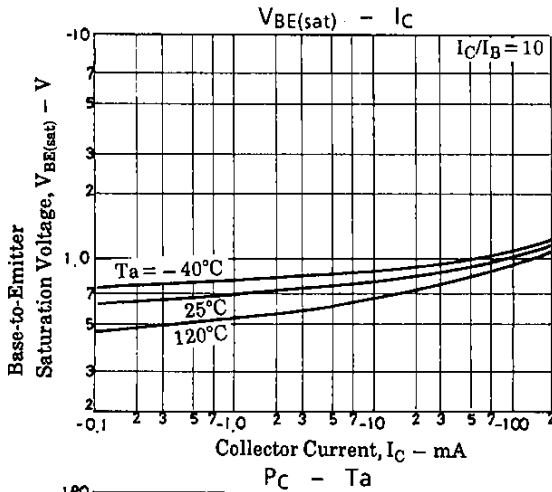
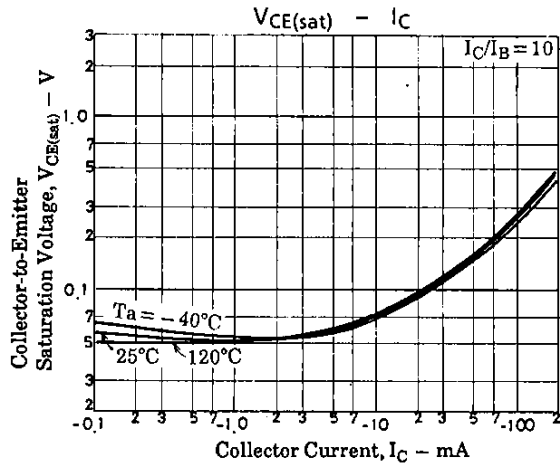
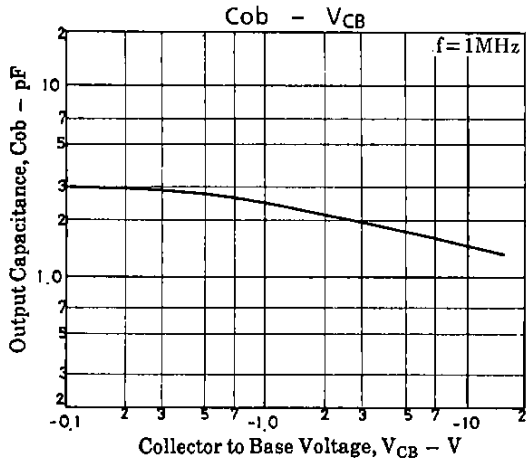
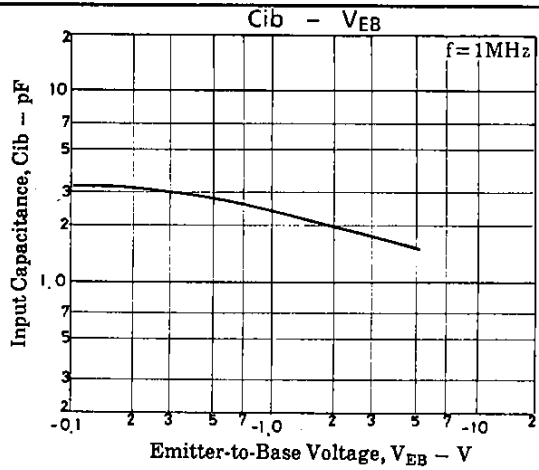
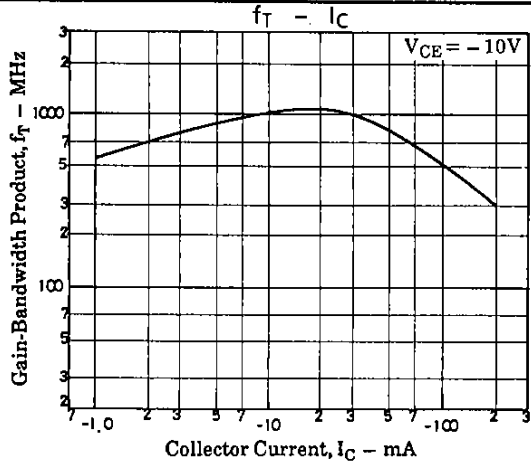


t_{off} Test Waveform ($V_{BB} = -8.0V$)



t_{stg} Test Waveform





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